Search History ('15pp) [signature] (9/16/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	96	spacer near4 (silicon adj nitride ("Si.sub.3" near1 "N.sub.4")) and passivation near4 ((silicon adj oxide) (silicon adj dioxide) ("Si" near1 "O.sub."$3) ("SiO.sub."$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:55
L2	11613	((257/288) or (257/296) or (257/321) or (257/344) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413) or (257/e21.626) or (257/e21.64) or (257/900)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 14:52
L3	11	1 and 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 14:53
L4	839650	interference search:	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:56
L5	0	((thick$5 near8 gate) (bird$2 adj beak)).ti,ab,clm. and ((gate near1 oxide) MOS MOSFET).ti,ab,clm. and ("WSi"$3 tungsten adj silicide).ti,ab,clm. and spacer near4 (silicon adj nitride ("Si.sub."$3 near1 "N.sub.4"$3) "Si.sub."$3"N.sub."$3).ti,ab,clm. and passivat$3 near4 (silicon adj $2oxide "SiO.sub."$3).clm,ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:01
S1	5	"272,968".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:50
S2	1	"5612249".PN.	USPAT	OR	OFF	2002/05/22 14:58
S3	1	"5637514".PN.	USPAT	OR	OFF	2002/05/22 14:59
S4	1	"5798550".PN.	USPAT	OR	OFF	2002/05/22 14:59
S5	1	"6015736".PN.	USPAT	OR	OFF	2002/05/22 15:00
S6	3	("5306655").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 15:43

S7	3	("5360758").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:03
S8	301	((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and "257"/$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 09:41
S9	3	("5382533").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:51
S10	3	("5679968").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:52
S11	3	("5714413").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:53
S12	0	("ep-621632$-$.did.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:53
S13	0	("ep-621632$-$.did.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:53
S14	0	rajeevakumar.in. and dram adj cell adj structure	EPO	OR	ON	2002/05/22 17:55
S15	6	rajeevakumar.in. and dram adj cell adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/22 17:55

S16	3	("5612249").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 10:42
S17	0	earom and selection same transistor same dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:43
S18	27	earom and transistor same dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:44
S19	6	earom and transistor same dram. ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:45
S20	109394	earom.ti,ab. and dram.ti,ab. and "257"/$6.ccls. or "438"/$6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:46
S21	5	earom.ti,ab. and dram.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:47
S22	187	selection near12 (transistor or fet or mosfet) near12 dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:49
S23	44	(selection near6 (transistor or fet or mosfet) near6 dram) and ("257"/$6.ccls. or "438"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 12:09
S24	3	("5854500").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 12:14

S25	2	("6037639").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 13:57
S26	1962	(257/296).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 12:26
S27	1041	(257/401).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 15:08
S28	432	(257/410).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 15:08
S29	2	("5885553").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/06 10:35
S30	2	("5612249").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/06 12:04
S31	0	(side adj wall or sidewall) near12 gate adj oxide near12 silicon adj nitride adj spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 12:06
S32	15	(side adj wall or sidewall) near12 gate adj oxide near12 silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 12:07
S33	147	oxidation adj barrier near4 oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 13:06

S34	201	(MOS or MOSFET).ti,ab,clm. and silicon adj nitride near4 (sidewall or side adj wall) near4 spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 13:09
S35	3702	((257/296) or (257/401) or (257/410)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/06 16:38
S36	0	(((257/296) or (257/401) or (257/410)).CCLS.) and "bird's beak" near4 gate near4 underneath and silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 16:39
S37	2	("5612249").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/04/15 14:10
S38	259	oxide near2 spacer near6 nitride and (mosfet or mos adj device or field adj effect adj transistor).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/15 14:15
S39	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/08 10:23
S40	2	("5612249").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 10:24
S41	2	("5907777").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 11:43
S42	4300	((257/296) or (257/401) or (257/410)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 11:44

S43	8	(((257/296) or (257/401) or (257/410)).CCLS.) and "bird's beak"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 11:44
S44	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/13 16:40
S45	30	(US-5854500-$ or US-5880496-$ or US-5969382-$ or US-6121651-$ or US-4610078-$ or US-5473179-$ or US-5939761-$ or US-6025215-$ or US-5907777-$ or US-5923965-$ or US-6114735-$ or US-6127710-$ or US-5637514-$ or US-5306655-$ or US-5360758-$ or US-6015736-$ or US-5798550-$ or US-5612249-$ or US-6281079-$ or US-6180978-$ or US-6037639-$ or US-5929492-$ or US-5382533-$ or US-5714413-$ or US-5679968-$ or US-5706164-$).did. or (US-20030042551-$ or US-20010041398-$ or US-20010033006-$).did. or (JP-05129595-$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2004/09/13 16:52
S46	3	((US-5854500-$ or US-5880496-$ or US-5969382-$ or US-6121651-$ or US-4610078-$ or US-5473179-$ or US-5939761-$ or US-6025215-$ or US-5907777-$ or US-5923965-$ or US-6114735-$ or US-6127710-$ or US-5637514-$ or US-5306655-$ or US-5360758-$ or US-6015736-$ or US-5798550-$ or US-5612249-$ or US-6281079-$ or US-6180978-$ or US-6037639-$ or US-5929492-$ or US-5382533-$ or US-5714413-$ or US-5679968-$ or US-5706164-$).did. or (US-20030042551-$ or US-20010041398-$ or US-20010033006-$).did. or (JP-05129595-$).did.) and ahmad. in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 16:52
S47	6	"272968".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/14 17:56
S48	1	"5306655".PN.	USPAT	OR	OFF	2004/09/14 16:48

S49	6	(("5306655") or ("5360655") or ("5612249") or ("5798550") or ("6015736") or ("5637514")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/09/14 17:59
S50	6	(("5306655") or ("5360758") or ("5612249") or ("5798550") or ("6015736") or ("5637514")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/09/14 17:59
S51	6	(US-5798550-$ or US-6015736-$ or US-5360758-$ or US-5612249-$ or US-5637514-$ or US-5306655-$).did.	USPAT	OR	OFF	2004/09/14 18:39
S52	7466	((257/288) or (257/296) or (257/321) or (257/344) or (257/368) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/09/14 18:40
S53	0	(((257/288) or (257/296) or (257/321) or (257/344) or (257/368) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413)).CCLS.) and silicon adj oxide adj passivation adj (layer film) and silicon adj nitride adj spacer and gate adj oxide.ti,ab, clm. and "bird's beak"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/14 18:42
S54	0	(((257/288) or (257/296) or (257/321) or (257/344) or (257/368) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413)).CCLS.) and silicon adj oxide near8 passivation adj (layer film) and silicon adj nitride near8 spacer and gate adj oxide.ti,ab, clm. and "bird's beak"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/14 18:42
S55	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 09:07
S56	20	"6037639"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 11:01
S57	21	"5612249"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 11:02

S58	3	(("6037639") or ("5612249") or ("5854500")).PN.	USPAT	OR	OFF	2005/02/16 15:24
S59	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 12:45
S60	2	isolating near2 metal adj silicide same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:47
S61	42	nitrogen near2 (migration barrier) near10 polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:48
S62	29	nitrogen near2 (migration barrier) near10 polysilicon same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:52
S63	0	nitrogen near2 (migration barrier) near10 polysilicon same gate adj stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:49
S64	427	silicide near3 barrier same polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:53
S65	240	(tungsten metal refractory) adj2 silicide near3 barrier same polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:54
S66	104	(tungsten metal refractory) adj2 silicide near3 barrier same polysilicon same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:54
S67	5	(tungsten metal refractory) adj2 silicide near3 barrier same polysilicon same gate adj stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:30

S68	373	(tungsten metal refractory) adj2 silicide near3 barrier.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:57
S69	65	(tungsten metal refractory) adj2 silicide near3 barrier.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:57
S70	131	gate adj stack and tungsten adj silicide near4 gate and polysilicon near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:27
S71	15	gate adj stack and ("WSi.sub.""42" tungsten adj silicide) near10 barrier near10 gate and polysilicon near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:28
S72	2	("5414301").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:31
S73	1	S72 and tungsten and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:32
S74	0	S72 and tungsten near8 barrier near8 silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:37
S75	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:39
S76	65	gate adj stack and tungsten adj silicide near10 gate near10 polysilicon near10 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:40
S77	7	gate adj stack and tungsten adj silicide near8 gate near8 polysilicon near8 silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:42

S78	1	gate adj stack and tungsten adj silicide near8 gate near8 polysilicon near8 silicon adj nitride and refractory adj metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:43
S79	1	gate adj stack and tungsten adj silicide near8 gate near8 polysilicon near8 silicon adj nitride and refractory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:43
S80	1	gate adj stack and tungsten adj silicide near10 gate near10 polysilicon near10 silicon adj nitride and refractory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:45
S81	103	(tungsten adj silicide "WSi.sub. "$2) near4 barrier and (polysilicon and silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:46
S82	72	(tungsten adj silicide "WSi.sub. "$2) near2 barrier and (polysilicon and silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:46
S83	27	(tungsten adj silicide "WSi.sub. "$2) near2 barrier adj layer and (polysilicon and silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:56
S84	1	metal adj diffusion adj barrier.ti.	IBM_TDB	OR	ON	2005/02/16 15:56
S85	152	tungsten adj silicide near3 barrier and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:12
S86	51	tungsten adj silicide near1 barrier and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 08:10
S87	11247	((257/288) or (257/296) or (257/321) or (257/344) or (257/368) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413) or (257/908)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/17 08:11

S88	7	S87 and tungsten adj silicide near1 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/17 08:12
S89	38	(US-20010033006-$ or US-20010041398-$ or US-20010050349-$ or US-20030042551-$ or US-20040124530-$).did. or (US-4610078-$ or US-5306655-$ or US-5360758-$ or US-5382533-$ or US-5473179-$ or US-5612249-$ or US-5637514-$ or US-5668394-$ or US-5679968-$ or US-5706164-$ or US-5714413-$ or US-5798550-$ or US-5854500-$ or US-5880496-$ or US-5907777-$ or US-5923965-$ or US-5923999-$ or US-5929492-$ or US-5939761-$ or US-5969382-$ or US-6015736-$ or US-6025215-$ or US-6037639-$ or US-6114735-$ or US-6114736-$ or US-6121651-$).did. or (US-6127710-$ or US-6180978-$ or US-6281079-$ or US-6455906-$ or US-6689658-$).did. or (JP-05129595-$).did. or (US-20010050349-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/16 13:00
S90	0	S89 and hung.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/16 13:00
S91	2	("6037639").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/16 13:12
S92	0	("885553.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/16 13:12
S93	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/10 22:21

S94	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/10 22:21
S95	6	S94	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/10 22:21
S96	6	"885553".AP.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/10 22:23
S97	2	("5965035").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/10 22:24
S98	2	("6037639").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/10 22:54
S99	75	heineck.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/10 22:54
S100	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/11 09:21
S101	54	"bird's beak" and GIDL	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/11 09:38
S102	2	nitride near2 spacer and oxide near2 passivat$3 and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/11 09:39
S103	2	nitride near2 spacer and oxide near2 passivat$3 and (gate adj induced adj drain adj leakage gidl)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/11 09:40

S104	29	nitride near2 spacer and oxide near2 passivat$3 and (mosfet mos mis misfet igfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/11 11:14
S105	0	(gate near2 (insulat$3 near4 oxide) gate near3 oxide).clm. and (MOS metal-on-oxide MOSFET MISFET MIS IGFET).clm. and (passivat$3 near4 ("Si.sub." near1 "O.sub."$2 "Si.sub."$4"O.sub."$4 silicon adj oxide silicon adj dioxide)).clm. and (silicon near4 nitride near4 spacer).clm. and (semiconductor silicon) near4 substrate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/11 11:24
S106	11995	((257/288) or (257/296) or (257/321) or (257/344) or (257/368) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/11 11:25
S107	2	S106 and (silicon adj nitride "Si.sub.3 N.sub.4") near4 spacer and (silicon oxide silicon dioxide "SiO.sub."$3) near4 passivat$3 and tungsten near4 gate and (polysilicon near4 gate poly adj gate poly-gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/11 11:31
S108	2	("6025227").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/11 11:29
S109	4	S106 and (silicon adj nitride "Si.sub.3 N.sub.4") near4 spacer and (silicon oxide silicon dioxide "SiO.sub."$3) near4 passivat$3 and tungsten near4 gate and (polysilicon near4 gate poly adj gate poly-gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/11 12:54
S110	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:15
S111	1	(US-20010033006-$).did.	US-PGPUB	OR	OFF	2005/09/15 16:15

S11 2	6	"272968".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/15 17:02
S11 3	1	de-19812212$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/15 17:02
S11 4	4	(MOS MOSFET MIS MISFET IGFET).ti,ab,clm. and memory.ti, ab,clm. and (semiconductor silicon) near1 substrate.ti,ab,clm. and (oxide near2 gate).ti,ab,clm. and (tungsten W).ti,ab,clm. and polysilicon.ti.ab,clm. and ("SiO. sub."$2 silicon adj (oxide dioxide)).ti,ab,clm. and (spacer near4 (silicon adj nitride ("Si.sub. 3" near1 "N.sub.4"))).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:24
S11 5	2685	ahmad.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:24

| S11 6 | 49 | (US-20010033006-$ or US-20010041398-$ or US-20010050349-$ or US-20030022429-$ or US-20030042551-$ or US-20040124530-$ or US-20040126948-$ or US-20040126968-$ or US-20030003651-$).did. or (US-4610078-$ or US-5306655-$ or US-5360758-$ or US-5382533-$ or US-5473179-$ or US-5612249-$ or US-5637514-$ or US-5668394-$ or US-5679968-$ or US-5706164-$ or US-5714413-$ or US-5798550-$ or US-5854500-$ or US-5880496-$ or US-5907777-$ or US-5923965-$ or US-5923999-$ or US-5929492-$ or US-5939761-$ or US-5969382-$ or US-6015736-$ or US-6025215-$ or US-6037639-$ or US-6114735-$ or US-6114736-$ or US-6121651-$).did. or (US-6127710-$ or US-6137130-$ or US-6180978-$ or US-6281079-$ or US-6372618-$ or US-6455906-$ or US-6689658-$ or US-6784546-$ or US-6909151-$ or US-6429068-$).did. or (JP-05129595-$).did. or (DE-19812212-$ or US-20010050349-$ or JP-2001035936-$).did. | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/09/16 10:24 |
| S11 7 | 3 | S115 and S116 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/09/16 10:24 |